



High-end Power Semiconductor Manufacturer

ZP1000A 1000-1800V Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications



Average forward current		I _{FAV}	1000 A		
Repetitive peak reverse voltage		V _{RRM}	1000 – 1800 V		
V _{RRM} , V	1000	1200	1400	1600	1800
Voltage code	10	12	14	16	18
T _j , °C			-60 – 190		

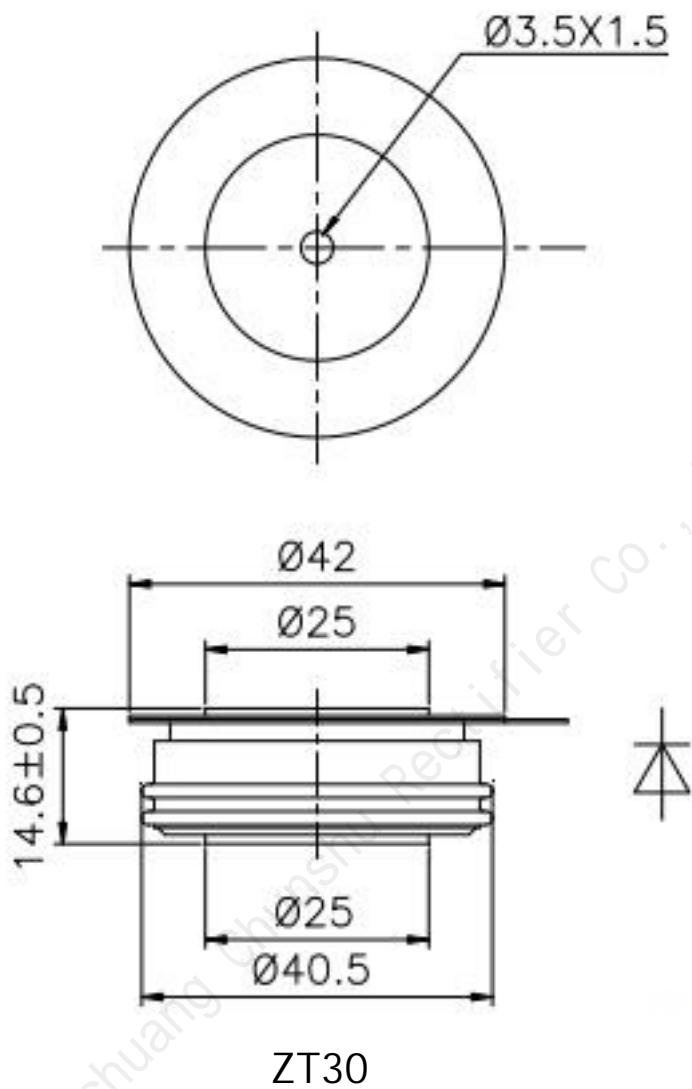
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Average forward current	A	1000	T _c =100 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FRMS}	RMS forward current	A	1570	T _c =117 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	15.0	T _j =T _j max	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			17.0	T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
I ² t	Safety factor	A ² s·10 ³	1125	T _j =T _j max	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			1445	T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
BLOCKING			1060	T _j =T _j max	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
V _{RRM}	Repetitive peak reverse voltages	V	1000 – 1800	T _{j min} < T _j < T _{j max} ;	180° half-sine wave; 50 Hz;
		V	1100 – 1900	T _{j min} < T _j < T _{j max} ;	180° half-sine wave; 50 Hz;single pulse;
V _R	Reverse continuous voltages	V	0.75·V _{RRM}	T _j =T _j max;	
THERMAL					
T _{stg}	Storage temperature	°C	-60 – 190		
T _j	Operating junction temperature	°C	-60 – 190		
MECHANICAL					
F	Mounting force	kN	9.0 – 11.0		
a	Acceleration	m/s ²	50 100	Device unclamped Device clamped	

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{FM}	Peak forward voltage, max	V	1.56	T _j =25 °C; I _{FM} =3140 A	
V _{F(TO)}	Forward threshold voltage, max	V	0.97	T _j =T _{j max} ;	
r _T	Forward slope resistance, max	mΩ	0.360	0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}	
BLOCKING					
I _{RRM}	Repetitive peak reverse current, max	mA	50	T _j =T _{j max} ; V _R =V _{RRM}	
THERMAL					
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.040	Direct current	Double side cooled
R _{thjc-A}			0.088		Anode side cooled
R _{thjc-K}			0.072		Cathode side cooled
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.009	Direct current	
MECHANICAL					
w	Weight, typ	g	110		
D _s	Surface creepage distance	mm (inch)	11.10 (0.437)		
D _a	Air strike distance	mm (inch)	11.60 (0.457)		

OVERALL DIMENSIONS



All dimensions in millimeters